L Number	Hits	Search Text	DB	Time stamp
101	0	wafer same photoexcitation same galvanic	USPAT;	2004/08/18 13:39
		. , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	2001,00,10 13:33
	1		DERWENT;	
1.00			IBM_TDB	
102	1	wafer same photoexcitation same wavelength	USPAT;	2004/08/18 13:40
	İ		EPO; JPO;	
			DERWENT;	
103	84	wafer and photoexcitation and wavelength	IBM_TDB	0004/00/40 45 55
103	04	water and photoexcitation and wavelength	USPAT; EPO; JPO;	2004/08/18 15:05
			DERWENT;	
			IBM TDB	
104	121	wafer and electromotive and wavelength	USPAT;	2004/08/18 15:04
1			EPO; JPO;	2001,00,10 10.01
			DERWENT;	
1.05	1	_	IBM_TDB	
105	121	wafer and photoexcitation	USPAT;	2004/08/18 14:13
	1		EPO; JPO;	
			DERWENT;	· ·
106	489	substrate and elegtnemetics and access and	IBM_TDB	0001100100
1 ***	409	substrate and electromotive and wavelength	USPAT;	2004/08/18 15:05
			EPO; JPO; DERWENT;	
			IBM TDB	
107	120	substrate and photoexcitation and	USPAT;	2004/08/18 15:05
		wavelength and clean\$4	EPO; JPO;	2001,00710 13.05
			DERWENT;	
100			IBM_TDB	
108	750	substrate same (laser or irradiated or	USPĀT;	2004/08/18 15:11
		irradiating) same clean\$4 same (UV or	EPO; JPO;	!
		ultraviolet or wavelength)	DERWENT;	
109	12	substrate same (laser or irradiated or	IBM_TDB	
1 103	12	irradiating) same clean\$4 same (UV or	USPAT;	2004/08/18 15:10
		ultraviolet or wavelength) same wiring	EPO; JPO; DERWENT;	
	1	and a state of wavelength, same willing	IBM TDB	
110	290	substrate same (laser or irradiated or	USPAT;	2004/08/18 15:25
	,	irradiating) same clean\$4 same wavelength	EPO; JPO;	2551,00,10 13.25
		-	DERWENT;	
	4.05		IBM_TDB	ļ
111	105	wafer same (laser or irradiated or	USPAT;	2004/08/18 15:34
		irradiating) same clean\$4 same wavelength	EPO; JPO;	
			DERWENT;	
112	695	wafer and wiring and (laser or irradiated	IBM_TDB USPAT;	2004/00/10 15 26
ĺ		or irradiating) and clean\$4 and	EPO; JPO;	2004/08/18 15:36
		wavelength	DERWENT;	
	!		IBM TDB	<u> </u>
113	184	wafer and wiring and (laser or irradiated	USPAT;	2004/08/18 15:56
		or irradiating) and clean\$4 and "500 nm"	EPO; JPO;	
		\cdot	DERWENT;	
114			IBM_TDB	
115	695	wafer and wiring and (laser or irradiated	USPAT	2004/08/18 15:39
] " "	or irradiating) and clean\$4 and wavelength	USPAT; EPO; JPO;	2004/08/18 15:57
	[g, and oreally and waverength	DERWENT;	
			IBM TDB	
116	40	wafer and wiring and (laser or irradiated	USPAT;	2004/08/18 16:05
		or irradiating) and clean\$4 and wavelength	EPO; JPO;	20.00
		and "PN junction"	DERWENT;	
117			IBM_TDB	
117	695	wafer and wiring and (laser or irradiated	USPAT;	2004/08/18 16:06
İ	[or irradiating) and clean\$4 and wavelength	EPO; JPO;	
			DERWENT;	
118	69	wafer and wiring and (laser or irradiated	IBM_TDB	2004/00/10 15 25
		or irradiating) and clean\$4 and wavelength	USPAT; EPO; JPO;	2004/08/18 16:06
		and CMP	DERWENT;	
			IBM TDB	
119	1		USPĀT	2004/08/18 16:06